



SOT-23 Plastic-Encapsulate Transistors

2SA1162 TRANSISTOR (PNP)

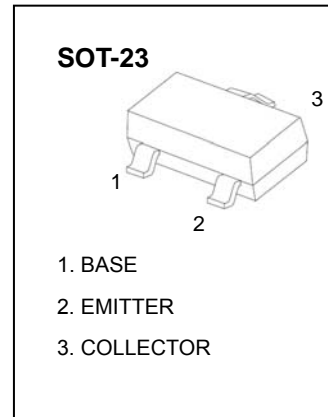
FEATURES

- . Low noise
- . Complementary to 2SC2712
- . Small Package

MARKING: SO , SY , SG

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-150	mA
P _C	Collector Power Dissipation	150	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	833	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 +150	°C

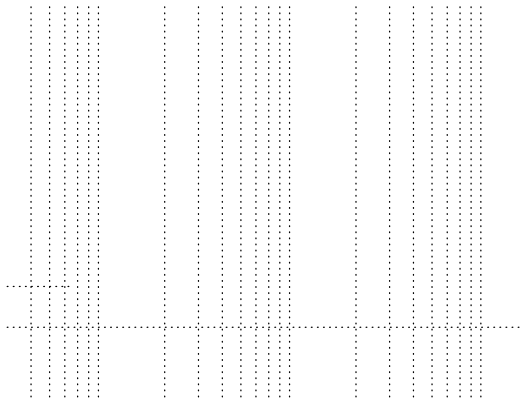
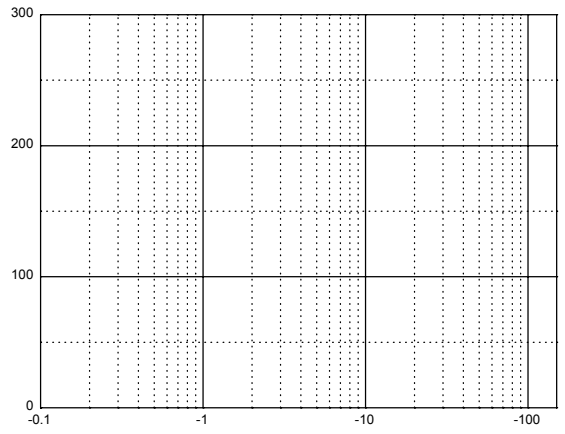


ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-6V, I _C =-2mA	70		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-1mA	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			7	pF
Noise figure	NF	V _{CE} =-6V, I _C =0.1mA, f=1KHz, R _g =10K			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR(G)
Range	70-140	120-240	200-400



Note:
1. Controlling dim.

